



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China





MACRONIX
INTERNATIONAL Co., LTD.

MX29GL128F

MX29GL128F

DATASHEET

Contents

FEATURES	5
PIN CONFIGURATION	6
PIN DESCRIPTION	7
BLOCK DIAGRAM	8
BLOCK DIAGRAM DESCRIPTION	9
BLOCK STRUCTURE	10
Table 1: SECTOR ARCHITECTURE	10
BUS OPERATION	11
Table 2-1. BUS OPERATION	11
Table 2-2. BUS OPERATION	12
FUNCTIONAL OPERATION DESCRIPTION	13
READ OPERATION	13
PAGE READ.....	13
WRITE OPERATION.....	13
DEVICE RESET	13
STANDBY MODE	13
OUTPUT DISABLE	14
BYTE/WORD SELECTION	14
HARDWARE WRITE PROTECT.....	14
ACCELERATED PROGRAMMING OPERATION	14
WRITE BUFFER PROGRAMMING OPERATION	14
SECTOR PROTECT OPERATION	15
AUTOMATIC SELECT BUS OPERATIONS.....	15
SECTOR LOCK STATUS VERIFICATION	15
READ SILICON ID MANUFACTURER CODE.....	16
READ INDICATOR BIT (Q7) FOR SECURITY SECTOR	16
INHERENT DATA PROTECTION.....	16
COMMAND COMPLETION.....	16
LOW VCC WRITE INHIBIT	16
WRITE PULSE "GLITCH" PROTECTION.....	16
LOGICAL INHIBIT	16
POWER-UP SEQUENCE	17
POWER-UP WRITE INHIBIT	17
POWER SUPPLY DECOUPLING	17
COMMAND OPERATIONS	18
READING THE MEMORY ARRAY	18
AUTOMATIC PROGRAMMING OF THE MEMORY ARRAY	18
ERASING THE MEMORY ARRAY	19
SECTOR ERASE	19

CHIP ERASE.....	20
ERASE SUSPEND/RESUME	21
SECTOR ERASE RESUME	21
PROGRAM SUSPEND/RESUME	22
PROGRAM RESUME	22
BUFFER WRITE ABORT	22
AUTOMATIC SELECT OPERATIONS	23
AUTOMATIC SELECT COMMAND SEQUENCE	23
READ MANUFACTURER ID OR DEVICE ID	24
RESET	24
ADVANCED SECTOR PROTECTION/UN-PROTECTION	25
Figure 1. Advance Sector Protection/Unprotection SPB Program Algorithm	25
1. Lock Register	26
Figure 2. Lock Register Program Algorithm	26
2. Solid write (non-volatile) protection Mode	27
Figure 3. SPB Program Algorithm	28
3. Solid Protection Bit Lock Bit	29
4. Password Protection Method	29
Sector Protection Status Table	30
SECURITY SECTOR FLASH MEMORY REGION	31
Factory Locked: Security Sector Programmed and Protected at the Factory	31
Customer Lockable: Security Sector NOT Programmed or Protected at the Factory	31
TABLE 3. COMMAND DEFINITIONS	32
COMMON FLASH MEMORY INTERFACE (CFI) MODE	35
QUERY COMMAND AND COMMAND FLASH MEMORY INTERFACE (CFI) MODE	35
Table 4-1. CFI mode: Identification Data Values	35
Table 4-2. CFI mode: System Interface Data Values	35
Table 4-3. CFI mode: Device Geometry Data Values.....	36
Table 4-4. CFI mode: Primary Vendor-Specific Extended Query Data Values.....	37
ELECTRICAL CHARACTERISTICS	38
ABSOLUTE MAXIMUM STRESS RATINGS.....	38
OPERATING TEMPERATURE AND VOLTAGE.....	38
Maximum Negative Overshoot Waveform.....	38
Maximum Positive Overshoot Waveform	38
DC CHARACTERISTICS	39
SWITCHING TEST CIRCUITS.....	40
SWITCHING TEST WAVEFORMS	40
AC CHARACTERISTICS	41
WRITE OPERATION.....	43
Figure 4. COMMAND WRITE OPERATION.....	43
READ/RESET OPERATION	44
Figure 5. READ TIMING WAVEFORMS	44

Figure 6. RESET# TIMING WAVEFORM.....	45
ERASE/PROGRAM OPERATION	46
Figure 7. AUTOMATIC CHIP ERASE TIMING WAVEFORM	46
Figure 8. AUTOMATIC CHIP ERASE ALGORITHM FLOWCHART.....	47
Figure 9. AUTOMATIC SECTOR ERASE TIMING WAVEFORM.....	48
Figure 10. AUTOMATIC SECTOR ERASE ALGORITHM FLOWCHART	49
Figure 11. ERASE SUSPEND/RESUME FLOWCHART.....	50
Figure 12. AUTOMATIC PROGRAM TIMING WAVEFORMS	51
Figure 13. ACCELERATED PROGRAM TIMING DIAGRAM.....	51
Figure 14. CE# CONTROLLED WRITE TIMING WAVEFORM.....	52
Figure 15. AUTOMATIC PROGRAMMING ALGORITHM FLOWCHART.....	53
Figure 16. SILICON ID READ TIMING WAVEFORM.....	54
WRITE OPERATION STATUS.....	55
Figure 17. DATA# POLLING TIMING WAVEFORMS (DURING AUTOMATIC ALGORITHMS).....	55
Figure 18. STATUS POLLING FOR WORD PROGRAM/ERASE	56
Figure 19. STATUS POLLING FOR WRITE BUFFER PROGRAM.....	57
Figure 20. TOGGLE BIT TIMING WAVEFORMS (DURING AUTOMATIC ALGORITHMS).....	58
Figure 21. TOGGLE BIT ALGORITHM.....	59
Figure 22. BYTE# TIMING WAVEFORM FOR READ OPERATIONS (BYTE# switching from byte mode to word mode)	60
Figure 23. PAGE READ TIMING WAVEFORM	61
Figure 24. DEEP POWER DOWN MODE WAVEFORM	62
Figure 25. WRITE BUFFER PROGRAM FLOWCHART	63
RECOMMENDED OPERATING CONDITIONS.....	64
At Device Power-Up.....	64
Figure A. AC Timing at Device Power-Up.....	64
ERASE AND PROGRAMMING PERFORMANCE	65
DATA RETENTION	65
LATCH-UP CHARACTERISTICS	65
PIN CAPACITANCE.....	65
ORDERING INFORMATION	66
PART NAME DESCRIPTION.....	67
PACKAGE INFORMATION.....	68
REVISION HISTORY	71

SINGLE VOLTAGE 3V ONLY FLASH MEMORY**FEATURES****GENERAL FEATURES**

- Power Supply Operation
 - 2.7 to 3.6 volt for read, erase, and program operations
 - MX29GL128F H/L: VI/O=VCC=2.7V~3.6V, VI/O voltage must tight with VCC
 - MX29GL128F U/D: VI/O=1.65V~3.6V for Input/Output
- Byte/Word mode switchable
 - 16,777,216 x 8 / 8,388,608 x 16
- 64KW/128KB uniform sector architecture
 - 128 equal sectors
- 16-byte/8-word page read buffer
- 64-byte/32-word write buffer
- Extra 128-word sector for security
 - Features factory locked and identifiable, and customer lockable
- Advanced sector protection function (Solid and Password Protect)
- Latch-up protected to 100mA from -1V to 1.5xVcc
- Low Vcc write inhibit : Vcc ≤ VLKO
- Compatible with JEDEC standard
 - Pinout and software compatible to single power supply Flash
- Deep power down mode

PERFORMANCE

- High Performance
 - Fast access time:
 - MX29GL128F H/L: 70/90ns (VCC=2.7~3.6V)
 - MX29GL128F U/D: 90/110ns (VCC=2.7~3.6V, V I/O=1.65V to Vcc)
 - Page access time:
 - MX29GL128F H/L: 25ns
 - MX29GL128F U/D: 30ns
 - Fast program time: 11us/word
 - Fast erase time: 0.6s/sector
- Low Power Consumption
 - Low active read current: 20mA (typical) at 5MHz
 - Low standby current: 30uA (typical)
- Minimum 100,000 erase/program cycle
- 20 years data retention

SOFTWARE FEATURES

- Program/Erase Suspend & Program/Erase Resume
 - Suspends sector erase operation to read data from or program data to another sector which is not being erased
 - Suspends sector program operation to read data from another sector which is not being program
- Status Reply
 - Data# Polling & Toggle bits provide detection of program and erase operation completion
- Support Common Flash Interface (CFI)

HARDWARE FEATURES

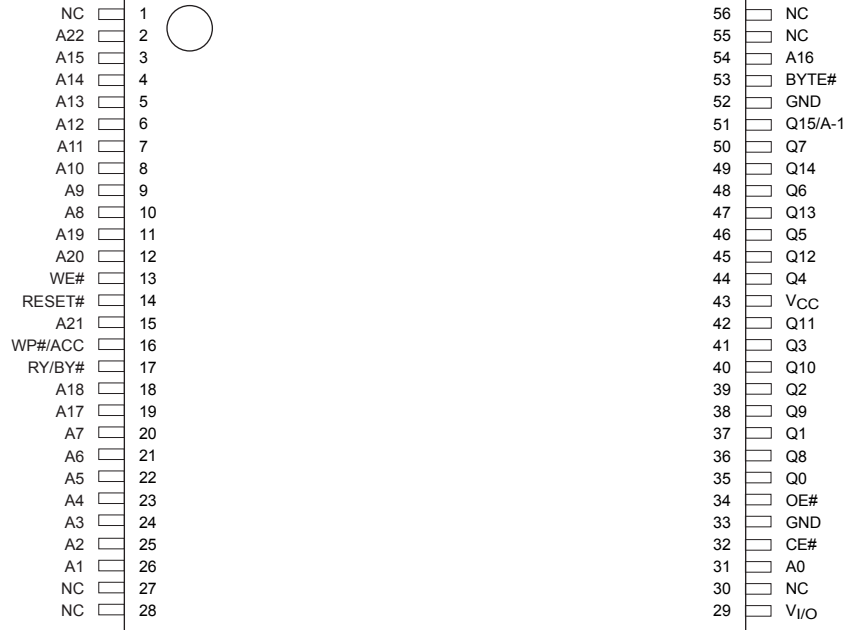
- Ready/Busy# (RY/BY#) Output
 - Provides a hardware method of detecting program and erase operation completion
- Hardware Reset (RESET#) Input
 - Provides a hardware method to reset the internal state machine to read mode
- WP#/ACC input pin
 - Hardware write protect pin/Provides accelerated program capability

PACKAGE

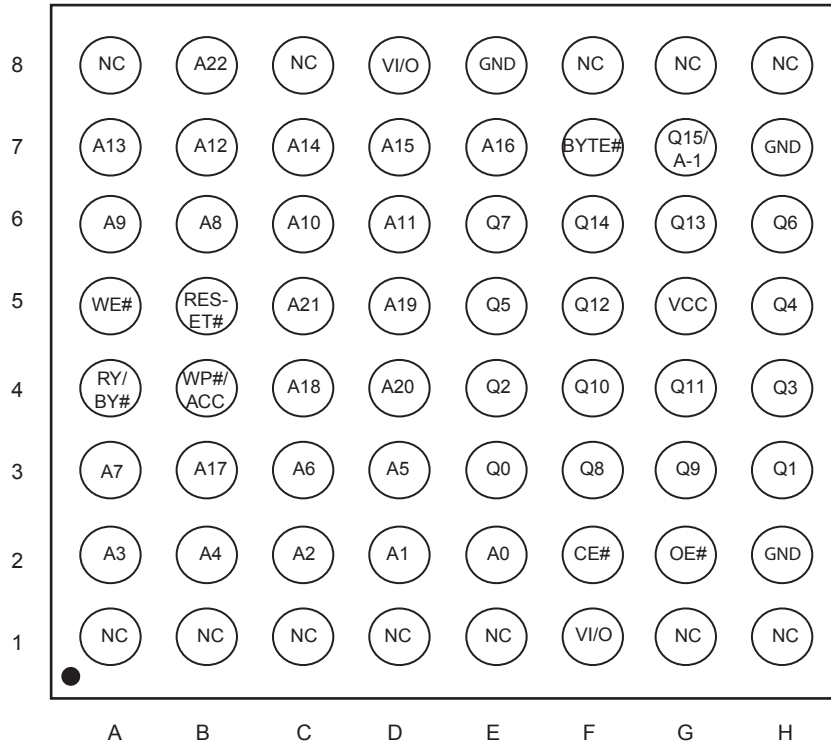
- 56-Pin TSOP
- 56-Ball FBGA (7mm x 9mm)
- 64-Ball LFBGA (11mm x 13mm)
- **All devices are RoHS Compliant**

PIN CONFIGURATION

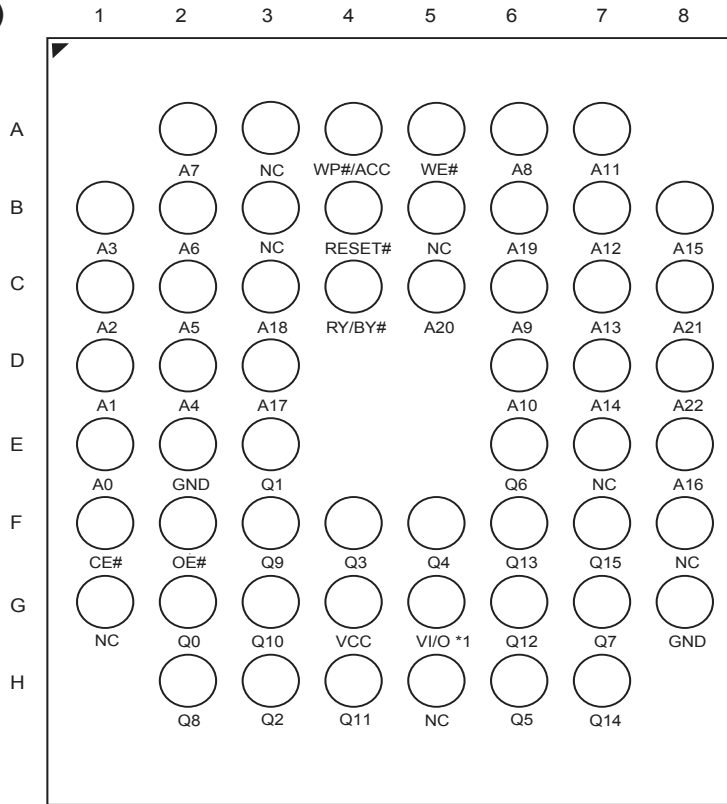
56 TSOP



64 LFBGA



56 FBGA (7x9x1.2mm)

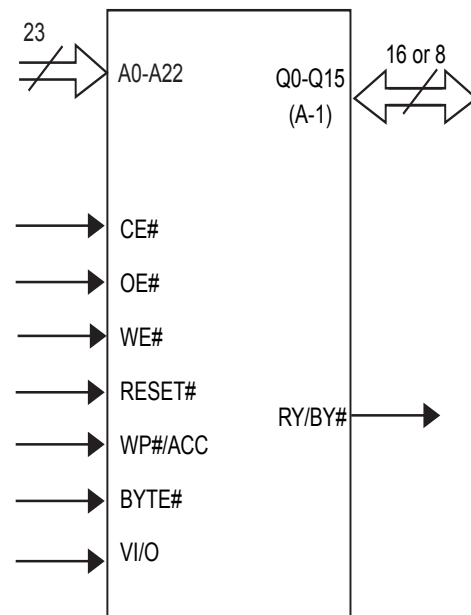


Note: *1. G5 pin is NC on MX29GL128F H/L.
*2. Only support word mode for 56-FBGA.

PIN DESCRIPTION

SYMBOL	PIN NAME
A0~A22	Address Input
Q0~Q14	Data Inputs/Outputs
Q15/A-1	Q15(Word Mode)/LSB addr(Byte Mode)
CE#	Chip Enable Input
WE#	Write Enable Input
OE#	Output Enable Input
RESET#	Hardware Reset Pin, Active Low
WP#/ACC*	Hardware Write Protect/Programming Acceleration input
RY/BY#	Ready/Busy Output
BYTE#	Selects 8 bits or 16 bits mode
VCC	+3.0V single power supply
GND	Device Ground
NC	Pin Not Connected Internally
VI/O	Power Supply for Input/Output

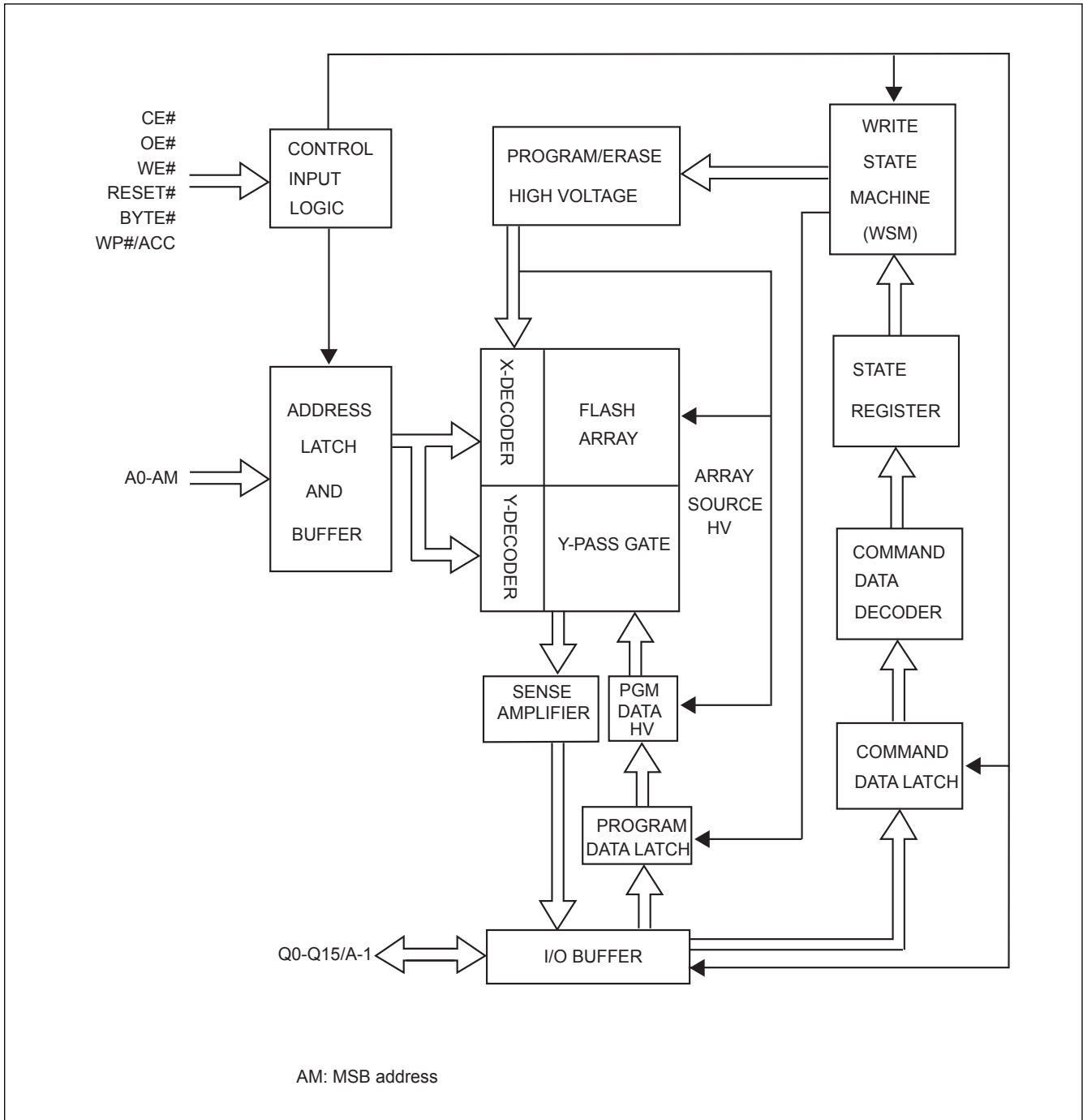
LOGIC SYMBOL



Notes:

1. WP#/ACC has internal pull up.
2. For MX29GL128F H/L VI/O voltage must tight with VCC.

BLOCK DIAGRAM



BLOCK DIAGRAM DESCRIPTION

The [block diagram](#) illustrates a simplified architecture of this device. Each block in the block diagram represents one or more circuit modules in the real chip used to access, erase, program, and read the memory array.

The "CONTROL INPUT LOGIC" block receives input pins CE#, OE#, WE#, RESET#, BYTE#, and WP#/ACC. It creates internal timing control signals according to the input pins and outputs to the "ADDRESS LATCH AND BUFFER" to latch the external address pins A0-AM(A22). The internal addresses are output from this block to the main array and decoders composed of "X-DECODER", "Y-DECODER", "Y-PASS GATE", AND "FLASH ARRAY". The X-DECODER decodes the word-lines of the flash array, while the Y-DECODER decodes the bit-lines of the flash array. The bit lines are electrically connected to the "SENSE AMPLIFIER" and "PGM DATA HV" selectively through the Y-PASS GATES. SENSE AMPLIFIERS are used to read out the contents of the flash memory, while the "PGM DATA HV" block is used to selectively deliver high power to bit-lines during programming. The "I/O BUFFER" controls the input and output on the Q0-Q15/A-1 pads. During read operation, the I/O BUFFER receives data from SENSE AMPLIFIERS and drives the output pads accordingly. In the last cycle of program command, the I/O BUFFER transmits the data on Q0-Q15/A-1 to "PROGRAM DATA LATCH", which controls the high power drivers in "PGM DATA HV" to selectively program the bits in a word or byte according to the user input pattern.

The "PROGRAM/ERASE HIGH VOLTAGE" block comprises the circuits to generate and deliver the necessary high voltage to the X-DECODER, FLASH ARRAY, and "PGM DATA HV" blocks. The logic control module comprises of the "WRITE STATE MACHINE, WSM", "STATE REGISTER", "COMMAND DATA DECODER", and "COMMAND DATA LATCH". When the user issues a command by toggling WE#, the command on Q0-Q15/A-1 is latched in the COMMAND DATA LATCH and is decoded by the COMMAND DATA DECODER. The STATE REGISTER receives the command and records the current state of the device. The WSM implements the internal algorithms for program or erase according to the current command state by controlling each block in the block diagram.

ARRAY ARCHITECTURE

The main flash memory array can be organized as Byte mode (x8) or Word mode (x16). The details of the address ranges and the corresponding sector addresses are shown in [Table 1](#).

BLOCK STRUCTURE**Table 1: SECTOR ARCHITECTURE**

Sector Size		Sector	Sector Address A22-A16	(x16) Address Range
Kbytes	Kwords			
128	64	SA0	000000xxx	000000h-00FFFFh
128	64	SA1	0000001xxx	010000h-01FFFFh
128	64	SA2	0000010xxx	020000h-02FFFFh
128	64	SA3	0000011xxx	030000h-03FFFFh
:	:	:	:	:
:	:	:	:	:
:	:	:	:	:
128	64	SA124	1111100xxx	7C0000h-7CFFFFh
128	64	SA125	1111101xxx	7D0000h-7DFFFFh
128	64	SA126	1111110xxx	7E0000h-7EFFFFh
128	64	SA127	1111111xxx	7F0000h-7FFFFFh

BUS OPERATION

Table 2-1. BUS OPERATION

Mode Select	RE-SET#	CE#	WE#	OE#	Address (Note4)	Data I/O Q7~Q0	Byte#		WP#/ACC
							Vil	Vih	
							Data (I/O) Q15~Q8		
Device Reset	L	X	X	X	X	HighZ	HighZ	HighZ	L/H
Standby Mode	Vcc ± 0.3V	Vcc± 0.3V	X	X	X	HighZ	HighZ	HighZ	H
Output Disable	H	L	H	H	X	HighZ	HighZ	HighZ	L/H
Read Mode	H	L	H	L	AIN	DOUT	Q8-Q14= HighZ, Q15=A-1	DOUT	L/H
Write	H	L	L	H	AIN	DIN		DIN	Note1,2
Accelerate Program	H	L	L	H	AIN	DIN		DIN	Vhv

Notes:

1. The first or last sector was protected if WP#/ACC=Vil.
2. When WP#/ACC = Vih, the protection conditions of the outmost sector depends on previous protection conditions. Refer to the advanced protect feature.
3. Q0~Q15 are input (DIN) or output (DOUT) pins according to the requests of command sequence, sector protection, or data polling algorithm.
4. In Word Mode (Byte#=Vih), the addresses are AM to A0, AM: MSB of address.
In Byte Mode (Byte#=Vil), the addresses are AM to A-1 (Q15), AM: MSB of address.

Table 2-2. BUS OPERATION

Item	Control Input			AM to A12	A11 to A10	A9	A8 to A7	A6	A5 to A4	A3 to A2	A1	A0	Q7 ~ Q0	Q15 ~ Q8
	CE#	WE#	OE#											
Sector Lock Status Verification	L	H	L	SA	X	V _{hv}	X	L	X	L	H	L	01h or 00h (Note 1)	X
Read Silicon ID Manufacturer Code	L	H	L	X	X	V _{hv}	X	L	X	L	L	L	C2H	X
Read Silicon ID -- MX29GL128F														
Cycle 1	L	H	L	X	X	V _{hv}	X	L	X	L	L	H	7EH	22H(Word), XXH(Byte)
Cycle 2	L	H	L	X	X	V _{hv}	X	L	X	H	H	L	21H	22H(Word), XXH(Byte)
Cycle 3	L	H	L	X	X	V _{hv}	X	L	X	H	H	H	01H	22H(Word), XXH(Byte)

Notes:

- Sector unprotected code:00h. Sector protected code:01h.
- Factory locked code: WP# protects high address sector: 99h.
WP# protects low address sector: 89h
Factory unlocked code: WP# protects high address sector: 19h.
WP# protects low address sector: 09h
- AM: MSB of address.

FUNCTIONAL OPERATION DESCRIPTION

READ OPERATION

To perform a read operation, the system addresses the desired memory array or status register location by providing its address on the address pins and simultaneously enabling the chip by driving CE# & OE# LOW, and WE# HIGH. After the Tce and Toe timing requirements have been met, the system can read the contents of the addressed location by reading the Data (I/O) pins. If either the CE# or OE# is held HIGH, the outputs will remain tri-stated and no data will appear on the output pins.

PAGE READ

This device is able to conduct Macronix MaskROM compatible high performance page read. Page size is 16 bytes or 8 words. The higher address Amax ~ A3 select the certain page, while A2~A0 for word mode, A2~A-1 for byte mode select the particular word or byte in a page. The page access time is Taa or Tce, following by Tpa for the rest of the page read time. When CE# toggles, access time is Taa or Tce. Page mode can be turned on by keeping "page-read address" constant and changing the "intra-read page" addresses.

WRITE OPERATION

To perform a write operation, the system provides the desired address on the address pins, enables the chip by asserting CE# LOW, and disables the Data (I/O) pins by holding OE# HIGH. The system then places data to be written on the Data (I/O) pins and pulses WE# LOW. The device captures the address information on the falling edge of WE# and the data on the rising edge of WE#. To see an example, please refer to the timing diagram in [Figure 4](#). The system is not allowed to write invalid commands (commands not defined in this datasheet) to the device. Writing an invalid command may put the device in an undefined state.

DEVICE RESET

Driving the RESET# pin LOW for a period of Trp or more will return the device to Read mode. If the device is in the middle of a program or erase operation, the reset operation will take at most a period of Tready1 before the device returns to Read mode. Until the device does returns to Read mode, the RY/BY# pin will remain Low (Busy Status).

When the RESET# pin is held at GND±0.3V, the device only consumes standby (Isbr) current. However, the device draws larger current if the RESET# pin is held at a voltage greater than GND+0.3V and less than or equal to Vil.

It is recommended to tie the system reset signal to the RESET# pin of the flash memory. This allows the device to be reset with the system and puts it in a state where the system can immediately begin reading boot code from it.

STANDBY MODE

The device enters Standby mode whenever the RESET# and CE# pins are both held High except in the embedded mode. While in this mode, WE# and OE# will be ignored, all Data Output pins will be in a high impedance state, and the device will draw minimal (Isb) current.

FUNCTIONAL OPERATION DESCRIPTION (cont'd)**OUTPUT DISABLE**

While in active mode (RESET# HIGH and CE# LOW), the OE# pin controls the state of the output pins. If OE# is held HIGH, all Data (I/O) pins will remain tri-stated. If held LOW, the Byte or Word Data (I/O) pins will drive data.

BYTE/WORD SELECTION

The BYTE# input pin is used to select the organization of the array data and how the data is input/output on the Data (I/O) pins. If the BYTE# pin is held HIGH, Word mode will be selected and all 16 data lines (Q0 to Q15) will be active.

If BYTE# is forced LOW, Byte mode will be active and only data lines Q0 to Q7 will be active. Data lines Q8 to Q14 will remain in a high impedance state and Q15 becomes the A-1 address input pin.

HARDWARE WRITE PROTECT

By driving the WP#/ACC pin LOW. The highest or lowest was protected from all erase/program operations. If WP#/ACC is held HIGH (Vih to VCC), these sectors revert to their previously protected/unprotected status.

ACCELERATED PROGRAMMING OPERATION

By applying high voltage (Vhv) to the WP#/ACC pin, the device will enter the Accelerated Programming mode. This mode permits the system to skip the normal command unlock sequences and program byte/word locations directly. During accelerated programming, the current drawn from the WP#/ACC pin is no more than ICP1.

WRITE BUFFER PROGRAMMING OPERATION

Programs 64bytes/32words in a programming operation. To trigger the Write Buffer Programming, start by the first two unlock cycles, then third cycle writes the Write Buffer Load command at the destined programming Sector Address. The forth cycle writes the "word locations subtract one" number.

Following above operations, system starts to write the mingling of address and data. After the programming of the first address or data, the "write-buffer-page" is selected. The following data should be within the above mentioned page.

The "write-buffer-page" is selected by choosing address Amax-A5.

"Write-Buffer-Page" address has to be the same for all address/ data write into the write buffer. If not, operation will ABORT.

To program the content of the write buffer page this command must be followed by a write to buffer Program confirm command.

The operation of write-buffer can be suspended or resumed by the standard commands, once the write buffer programming operation is finished, it'll return to normal READ mode.

FUNCTIONAL OPERATION DESCRIPTION (cont'd)**WRITE BUFFER PROGRAMMING OPERATION (cont'd)**

ABORT will be executed for the Write Buffer Programming Sequence if following condition occurs:

- The value loaded is bigger than the page buffer size during "Number of Locations to Program"
- Address written in a sector is not the same as the one assigned during the Write-Buffer-Load command.
- Address/ Data pair written to a different write-buffer-page than the one assigned by the "Starting Address" during the "write buffer data loading" operation.
- Writing not "Confirm Command" after the assigned number of "data load" cycles.

At Write Buffer Abort mode, the status register will be Q1=1, Q7=DATA# (last address written), Q6=toggle. A Write-to-Buffer-Abort Reset command sequence has to be written to reset the device for the next operation.

Write buffer programming can be conducted in any sequence. However the CFI functions, autoselect, Secured Silicon sector are not functional when program operation is in progress. Multiple write buffer programming operations on the same write buffer address range without intervening erases is available. Any bit in a write buffer address range can't be programmed from 0 back to 1.

SECTOR PROTECT OPERATION

The device provides user programmable protection operations for selected sectors. Please refer to [Table 1](#) which show all Sector assignments.

During the protection operation, the sector address of any sector may be used to specify the Sector being protected.

AUTOMATIC SELECT BUS OPERATIONS

The following five bus operations require A9 to be raised to V_hv. Please see AUTOMATIC SELECT COMMAND SEQUENCE in the COMMAND OPERATIONS section for details of equivalent command operations that do not require the use of V_hv.

SECTOR LOCK STATUS VERIFICATION

To determine the protected state of any sector using bus operations, the system performs a READ OPERATION with A9 raised to V_hv, the sector address applied to address pins A22 to A12, address pins A6, A3, A2 & A0 held LOW, and address pin A1 held HIGH. If data bit Q0 is LOW, the sector is not protected, and if Q0 is HIGH, the sector is protected.

FUNCTIONAL OPERATION DESCRIPTION (cont'd)

READ SILICON ID MANUFACTURER CODE

To determine the Silicon ID Manufacturer Code, the system performs a READ OPERATION with A9 raised to V_{hv} and address pins A6, A3, A2, A1, & A0 held LOW. The Macronix ID code of C2h should be present on data bits Q7 to Q0.

READ INDICATOR BIT (Q7) FOR SECURITY SECTOR

To determine if the Security Sector has been locked at the factory, the system performs a READ OPERATION with A9 raised to V_{hv}, address pin A6, A3 & A2 held LOW, and address pins A1 & A0 held HIGH. If the Security Sector has been locked at the factory, the code 99h(H)/89h(L) will be present on data bits Q7 to Q0. Otherwise, the factory unlocked code of 19h(H)/09h(L) will be present.

INHERENT DATA PROTECTION

To avoid accidental erasure or programming of the device, the device is automatically reset to Read mode during power up. Additionally, the following design features protect the device from unintended data corruption.

COMMAND COMPLETION

Only after the successful completion of the specified command sets will the device begin its erase or program operation. The failure in observing valid command sets will result in the memory returning to read mode.

LOW VCC WRITE INHIBIT

The device refuses to accept any program/erase command when V_{cc} is less than VL_{KO}. This prevents data from spuriously being altered during power-up, power-down, or temporary power interruptions. The device automatically resets itself when V_{cc} is lower than VL_{KO} and program/erase commands are ignored until V_{cc} is greater than VL_{KO}. The system must provide proper signals on control pins after V_{cc} rises above VL_{KO} to avoid unintentional program or erase operations.

WRITE PULSE "GLITCH" PROTECTION

CE#, WE#, OE# pulses shorter than 5ns are treated as glitches and will not be regarded as an effective write cycle.

LOGICAL INHIBIT

A valid write cycle requires both CE# and WE# at V_{il} with OE# at V_{ih}. Write cycle is ignored when either CE# at V_{ih}, WE# at V_{ih}, or OE# at V_{il}.

FUNCTIONAL OPERATION DESCRIPTION (cont'd)**POWER-UP SEQUENCE**

Upon power up, the device is placed in Read mode. Furthermore, program or erase operation will begin only after successful completion of specified command sequences.

POWER-UP WRITE INHIBIT

When WE#, CE# is held at V_{il} and OE# is held at V_{ih} during power up, the device ignores the first command on the rising edge of WE#.

POWER SUPPLY DECOUPLING

A 0.1 μ F capacitor should be connected between the Vcc and GND to reduce the noise effect.

COMMAND OPERATIONS

READING THE MEMORY ARRAY

Read mode is the default state after power up or after a reset operation. To perform a read operation, please refer to READ OPERATION in the BUS OPERATIONS section above.

If the device receives an Erase Suspend command while in the Sector Erase state, the erase operation will pause (after a time delay not exceeding 20us) and the device will enter Erase-Suspended Read mode. While in the Erase-Suspended Read mode, data can be programmed or read from any sector not being erased. Reading from addresses within sector (s) being erased will only return the contents of the status register, which is in fact how the current status of the device can be determined.

If a program command is issued to any inactive (not currently being erased) sector during Erase-Suspended Read mode, the device will perform the program operation and automatically return to Erase-Suspended Read mode after the program operation completes successfully.

While in Erase-Suspended Read mode, an Erase Resume command must be issued by the system to reactivate the erase operation. The erase operation will resume from where it was suspended and will continue until it completes successfully or another Erase Suspend command is received.

After the memory device completes an embedded operation (automatic Chip Erase, Sector Erase, or Program) successfully, it will automatically return to Read mode and data can be read from any address in the array. If the embedded operation fails to complete, as indicated by status register bit Q5 (exceeds time limit flag) going HIGH during the operations, the system must perform a reset operation to return the device to Read mode.

There are several states that require a reset operation to return to Read mode:

1. A program or erase failure--indicated by status register bit Q5 going HIGH during the operation. Failures during either of these states will prevent the device from automatically returning to Read mode.
2. The device is in Auto Select mode or CFI mode. These two states remain active until they are terminated by a reset operation.

In the two situations above, if a reset operation (either hardware reset or software reset command) is not performed, the device will not return to Read mode and the system will not be able to read array data.

AUTOMATIC PROGRAMMING OF THE MEMORY ARRAY

The device provides the user the ability to program the memory array in Byte mode or Word mode. As long as the user enters the correct *cycle* defined in the [Table 3](#) (including 2 unlock cycles and the A0H program command), any byte or word data provided on the data lines by the system will automatically be programmed into the array at the specified location.

After the program command sequence has been executed, the internal write state machine (WSM) automatically executes the algorithms and timings necessary for programming and verification, which includes generating suitable program pulses, checking cell threshold voltage margins, and repeating the program pulse if any cells do not pass verification or have low margins. The internal controller protects cells that do pass verification and margin tests from being over-programmed by inhibiting further program pulses to these passing cells as weaker cells continue to be programmed.

With the internal WSM automatically controlling the programming process, the user only needs to enter the program command and data once.

COMMAND OPERATIONS (cont'd)

AUTOMATIC PROGRAMMING OF THE MEMORY ARRAY (cont'd)

Programming will only change the bit status from "1" to "0". It is not possible to change the bit status from "0" to "1" by programming. This can only be done by an erase operation. Furthermore, the internal write verification only checks and detects errors in cases where a "1" is not successfully programmed to "0".

Any commands written to the device during programming will be ignored except hardware reset or program suspend. Hardware reset will terminate the program operation after a period of time no more than 10us. When the embedded program algorithm is complete or the program operation is terminated by a hardware reset, the device will return to Read mode. Program suspend ready, the device will enter program suspend read mode.

After the embedded program operation has begun, the user can check for completion by reading the following bits in the status register:

Status	Q7 ^{*1}	Q6 ^{*1}	Q5	Q1	RY/BY# (Note)
In progress	Q7#	Toggling	0	0	0
Exceed time limit	Q7#	Toggling	1	N/A	0

Note: RY/BY# is an open drain output pin and should be connected to VCC through a high value pull-up resistor.

ERASING THE MEMORY ARRAY

There are two types of erase operations performed on the memory array -- Sector Erase and Chip Erase. In the Sector Erase operation, one or more selected sectors may be erased simultaneously. In the Chip Erase operation, the complete memory array is erased except for any protected sectors. More details of the protected sectors are explained in section [Advanced Sector Protection/Un-protection](#).

SECTOR ERASE

The sector erase operation is used to clear data within a sector by returning all of its memory locations to the "1" state. It requires six command cycles to initiate the erase operation. The first two cycles are "unlock cycles", the third is a configuration cycle, the fourth and fifth are also "unlock cycles", and the sixth cycle is the Sector Erase command. After the sector erase command sequence has been issued, an internal 50us time-out counter is started. Until this counter reaches zero, additional sector addresses and Sector Erase commands may be issued thus allowing multiple sectors to be selected and erased simultaneously. After the 50us time-out counter has expired, no new commands will be accepted and the embedded sector erase operation will begin. *Note that the 50us timer-out counter is restarted after every erase command sequence.* If the user enters any command other than Sector Erase or Erase Suspend during the time-out period, the erase operation will abort and the device will return to Read mode.

After the embedded sector erase operation begins, all commands except Erase Suspend will be ignored. The only way to interrupt the operation is with an Erase Suspend command or with a hardware reset. The hardware reset will completely abort the operation and return the device to Read mode.

COMMAND OPERATIONS (cont'd)**SECTOR ERASE (cont'd)**

The system can determine the status of the embedded sector erase operation by the following methods:

Status	Q7	Q6	Q5	Q3 ^{*1}	Q2	RY/BY# ^{*2}
Time-out period	0	Toggling	0	0	Toggling	0
In progress	0	Toggling	0	1	Toggling	0
Exceeded time limit	0	Toggling	1	1	Toggling	0

Notes:

1. The Q3 status bit is the 50us time-out indicator. When Q3=0, the 50us time-out counter has not yet reached zero and a new Sector Erase command may be issued to specify the address of another sector to be erased. When Q3=1, the 50us time-out counter has expired and the Sector Erase operation has already begun. Erase Suspend is the only valid command that may be issued once the embedded erase operation is underway.
2. RY/BY# is open drain output pin and should be connected to VCC through a high value pull-up resistor.
3. When an attempt is made to erase only protected sector (s), the erase operation will abort thus preventing any data changes in the protected sector (s). Q7 will output "0" and Q6 will toggle briefly (100us or less) before aborting and returning the device to Read mode. If unprotected sectors are also specified, however, they will be erased normally and the protected sector (s) will remain unchanged.
4. Q2 is a localized indicator showing a specified sector is undergoing erase operation or not. Q2 toggles when user reads at addresses where the sectors are actively being erased (in erase mode) or to be erased (in erase suspend mode).

CHIP ERASE

The Chip Erase operation is used erase all the data within the memory array. All memory cells containing a "0" will be returned to the erased state of "1". This operation requires 6 write cycles to initiate the action. The first two cycles are "unlock" cycles, the third is a configuration cycle, the fourth and fifth are also "unlock" cycles, and the sixth cycle initiates the chip erase operation.

During the chip erase operation, no other software commands will be accepted, but if a hardware reset is received or the working voltage is too low, that chip erase will be terminated. After Chip Erase, the chip will automatically return to Read mode.

The system can determine the status of the embedded chip erase operation by the following methods:

Status	Q7	Q6	Q5	Q2	RY/BY# ^{*1}
In progress	0	Toggling	0	Toggling	0
Exceed time limit	0	Toggling	1	Toggling	0

*1: RY/BY# is open drain output pin and should be connected to VCC through a high value pull-up resistor.

COMMAND OPERATIONS (cont'd)**ERASE SUSPEND/RESUME**

After beginning a sector erase operation, Erase Suspend is the only valid command that may be issued. If system issues an Erase Suspend command during the 50us time-out period following a Sector Erase command, the time-out period will terminate immediately and the device will enter Erase-Suspended Read mode. If the system issues an Erase Suspend command after the sector erase operation has already begun, the device will not enter Erase-Suspended Read mode until 20us time has elapsed. The system can determine if the device has entered the Erase-Suspended Read mode through Q6, Q7, and RY/BY#.

After the device has entered Erase-Suspended Read mode, the system can read or program any sector (s) except those being erased by the suspended erase operation. Reading any sector being erased or programmed will return the contents of the status register. Whenever a suspend command is issued, user must issue a resume command and check Q6 toggle bit status, before issue another erase command. The system can use the status register bits shown in the following table to determine the current state of the device:

Status	Q7	Q6	Q5	Q3	Q2	Q1	RY/BY#
Erase suspend read in erase suspended sector	1	No toggle	0	N/A	toggle	N/A	1
Erase suspend read in non-erase suspended sector	Data	Data	Data	Data	Data	Data	1
Erase suspend program in non-erase suspended sector	Q7#	Toggle	0	N/A	N/A	N/A	0

When the device has suspended erasing, user can execute the command sets except sector erase and chip erase, such as read silicon ID, sector protect verify, program, CFI query and erase resume.

SECTOR ERASE RESUME

The sector Erase Resume command is valid only when the device is in Erase-Suspended Read mode. After erase resumes, the user can issue another Erase Suspend command, but there should be a 400us interval between Erase Resume and the next Erase Suspend command.

COMMAND OPERATIONS (cont'd)**PROGRAM SUSPEND/RESUME**

After beginning a program operation, Program Suspend is the only valid command that may be issued. The system can determine if the device has entered the Program-Suspended Read mode through Q6 and RY/BY#.

After the device has entered Program-Suspended mode, the system can read any sector (s) except those being programmed by the suspended program operation. Reading the sector being program suspended is invalid. Whenever a suspend command is issued, user must issue a resume command and check Q6 toggle bit status, before issue another program command. The system can use the status register bits shown in the following table to determine the current state of the device:

Status	Q7	Q6	Q5	Q3	Q2	Q1	RY/BY#
Program suspend read in program suspended sector	Invalid						1
Program suspend read in non-program suspended sector	Data	Data	Data	Data	Data	Data	1

When the device has Program/Erase suspended, user can execute read array, auto-select, read CFI, read security silicon.

PROGRAM RESUME

The Program Resume command is valid only when the device is in Program-Suspended mode. After program resumes, the user can issue another Program Suspend command, but there should be a 5us interval between Program Resume and the next Program Suspend command.

BUFFER WRITE ABORT

Q1 is the indicator of Buffer Write Abort. When Q1=1, the device will abort from buffer write and go back to read status register shown as following table:

Status	Q7	Q6	Q5	Q3	Q2	Q1	RY/BY#
Buffer Write Busy	Q7#	Toggle	0	N/A	N/A	0	0
Buffer Write Abort	Q7#	Toggle	0	N/A	N/A	1	0
Buffer Write Exceeded Time Limit	Q7#	Toggle	1	N/A	N/A	0	0

COMMAND OPERATIONS (cont'd)

AUTOMATIC SELECT OPERATIONS

When the device is in Read mode, Program Suspended mode, Erase-Suspended Read mode, or CFI mode, the user can issue the *Automatic Select* command shown in [Table 3](#) (two unlock cycles followed by the Automatic Select command 90h) to enter Automatic Select mode. After entering Automatic Select mode, the user can query the Manufacturer ID, Device ID, Security Sector locked status, or Sector protected status multiple times without issuing a new Automatic Select command.

While In Automatic Select mode, issuing a Reset command (F0h) will return the device to Read mode (or Ease-Suspended Read mode if Erase-Suspend was active) or Program Suspended Read mode if Program Suspend was active.

Another way to enter Automatic Select mode is to use one of the bus operations shown in [Table 2-2. BUS OPERATION](#). After the high voltage (V_{hv}) is removed from the A9 pin, the device will automatically return to Read mode or Erase-Suspended Read mode.

AUTOMATIC SELECT COMMAND SEQUENCE

Automatic Select mode is used to access the manufacturer ID, device ID and to verify whether or not secured silicon is locked and whether or not a sector is protected. The automatic select mode has four command cycles. The first two are unlock cycles, and followed by a specific command. The fourth cycle is a normal read cycle, and user can read at any address any number of times without entering another command sequence. The Reset command is necessary to exit the Automatic Select mode and back to read array. The following table shows the identification code with corresponding address.

		Address	Data (Hex)	Representation
Manufacturer ID	Word	X00	C2	
	Byte	X00	C2	
Device ID	Word	X01/0E/0F	227E/2221/2201	
	Byte	X02/1C/1E	7E/21/01	
Secured Silicon	Word	X03	99/19 (H)	Factory locked/unlocked
			89/09 (L)	
	Byte	X06	99/19 (H)	Factory locked/unlocked
			89/09 (L)	
Sector Protect Verify	Word	(Sector address) X 02	00/01	Unprotected/protected
	Byte	(Sector address) X 04	00/01	Unprotected/protected

After entering automatic select mode, no other commands are allowed except the reset command.

COMMAND OPERATIONS (cont'd)

READ MANUFACTURER ID OR DEVICE ID

The Manufacturer ID (identification) is a unique hexadecimal number assigned to each manufacturer by the JEDEC committee. Each company has its own manufacturer ID, which is different from the ID of all other companies. The number assigned to Macronix is C2h.

After entering Automatic Select mode, performing a read operation with A1 & A0 held LOW will cause the device to output the Manufacturer ID on the Data I/O (Q7 to Q0) pins.

RESET

In the following situations, executing reset command will reset device back to Read mode:

- Among erase command sequence (before the full command set is completed)
- Sector erase time-out period
- Erase fail (while Q5 is high)
- Among program command sequence (before the full command set is completed, erase-suspended program included)
- Program fail (while Q5 is high, and erase-suspended program fail is included)
- Auto-select mode
- CFI mode

While device is at the status of program fail or erase fail (Q5 is high), user must issue reset command to reset device back to read array mode. While the device is in Auto-Select mode or CFI mode, user must issue reset command to reset device back to read array mode.

When the device is in the progress of programming (not program fail) or erasing (not erase fail), device will ignore reset command.

ADVANCED SECTOR PROTECTION/UN-PROTECTION

There are two ways to implement software Advanced Sector Protection on this device: Password method or Solid methods. Through these two protection method, user can disable or enable the programming or erasing operation to any individual sector or whole chip. The figure below helps describe an overview of these methods.

The device is default to the Solid mode and all sectors are unprotected when shipped from factory. The detail algorithm of advance sector protection is shown as follows:

Figure 1. Advance Sector Protection/Unprotection SPB Program Algorithm

